

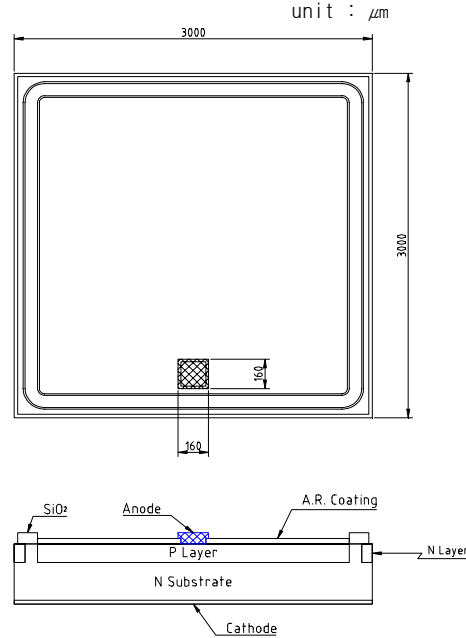
OPD3030

HIGH SPEED SENSITIVITY

Silicon PIN Photo Diode

1. Structure

- 1.1 Chip Size : 3.00mm X 3.00mm
- 1.2 Chip thickness : 400±20um
- 1.3 Metallization : Top - Al, Bottom - Au
- 1.4 Passivation : Silicon Oxide
- 1.5 Bonding Pad Size
- Anode(top) : 160um X 160um
- 1.6 Active Area : 2.86mm X 2.86mm



2. Electro-Optical Characteristics

(Ta=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Open Circuit Voltage	V_{OP}	0.3	0.32		V	Note(1)
Short Circuit Current	I_{SC}	69	86		μA	Note(1)
Spectrum Sensitivity	λ	430 ~ 1,100			nm	
Peak Sensing Wavelength	λ_P		940		nm	
Forward Voltage	V_F	0.5		1.3	V	$I_F=10mA$
Dark Current	I_D			10	nA	$V_R=10V$
Reverse Breakdown Voltage	B_{VR}	30			V	$I_R=10\mu A$

Note(1): Parallel light of 1,000Lux illumination is applied by a Tungsten lamp

3. Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Maximum rating	Unit
Reverse Breakdown Voltage	BVR	30	V
Junction Temperature	TJ	150	°C

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